

<b>SANYO</b>	No.1030E	<b>2SB926/2SD1246</b>
PNP/NPN Epitaxial Planar Silicon Transistors		
<b>Large-Current Driving Applications</b>		

**Applications**

- Power supplies, relay drivers, lamp drivers, electrical equipment

**Features**

- Adoption of FBET, MBIT processes
- Low saturation voltage
- Large current capacity and wide ASO

( ) : 2SB926

**Absolute Maximum Ratings/ $T_a = 25^\circ\text{C}$**

			unit
Collector to base voltage	$V_{CB0}$	(-)30	V
Collector to emitter voltage	$V_{CE0}$	(-)25	V
Emitter to base voltage	$V_{EBO}$	(-)6	V
Collector current	$I_C$	(-)2	A
Collector Current(Pulse)	$I_{CP}$	(-)5	A
Collector dissipation	$P_C$	0.75	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 ~ +150	$^\circ\text{C}$

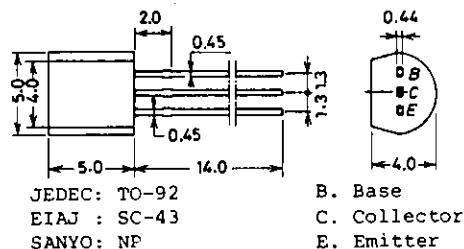
**Electrical Characteristics/ $T_a = 25^\circ\text{C}$**

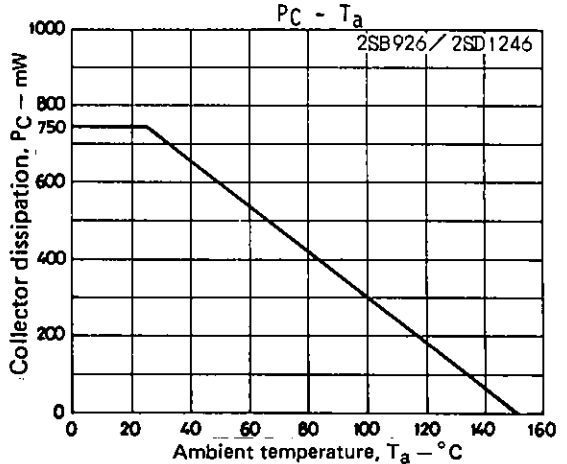
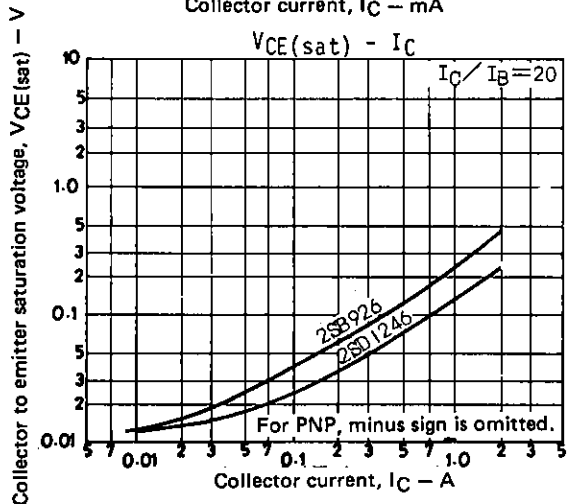
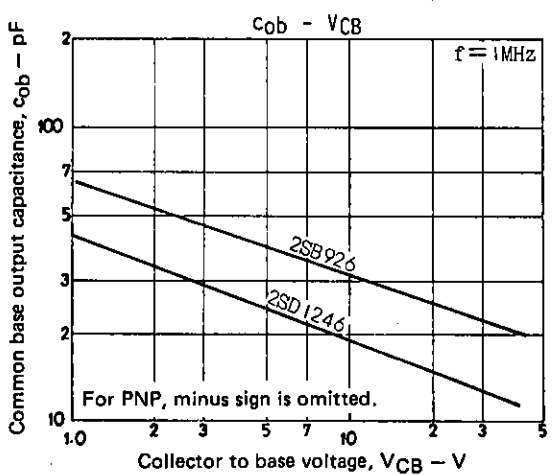
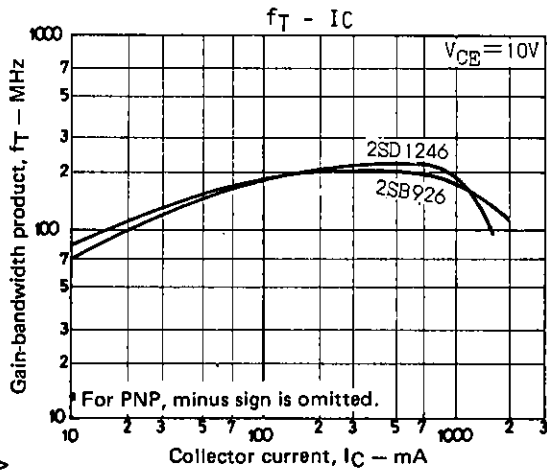
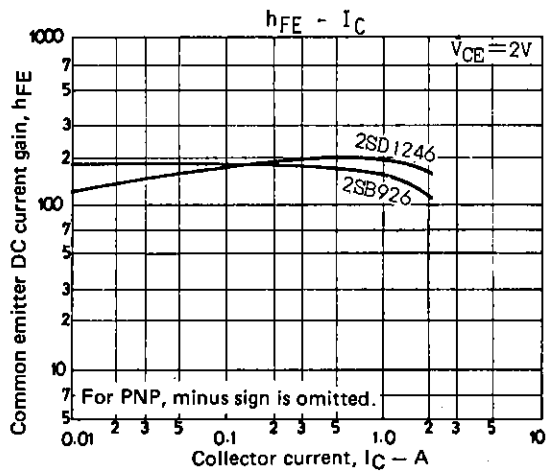
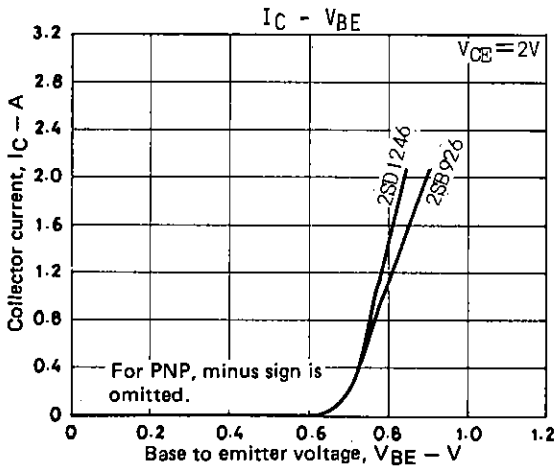
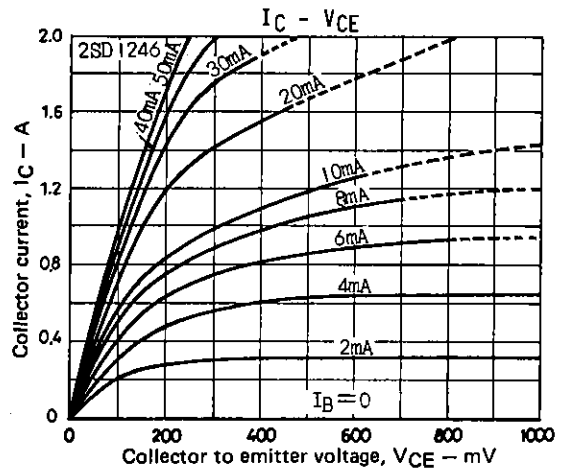
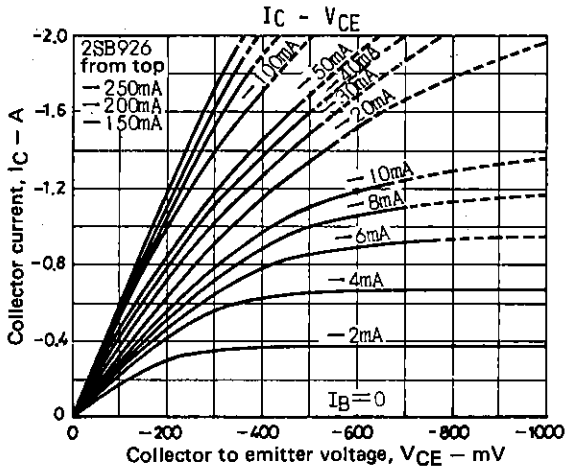
			min	typ	max	unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = (-)20\text{ V}, I_E = 0$			(-)0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = (-)4\text{ V}, I_C = 0$			(-)0.1	$\mu\text{A}$
DC current gain	$h_{FE}(1)$	$V_{CE} = (-)2\text{ V}, I_C = (-)100\text{ mA}$	100*		560*	
	$h_{FE}(2)$	$V_{CE} = (-)2\text{ V}, I_C = (-)1.5\text{ A, pulse}$	65	130		
Gain-bandwidth product	$f_T$	$V_{CE} = (-)10\text{ V}, I_C = (-)50\text{ mA}$		150		MHz
Common base output capacitance	$c_{ob}$	$V_{CB} = (-)10\text{ V}, f = 1\text{ MHz}$		19		pF
				(32)		
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = (-)1.5\text{ A}, I_B = (-)75\text{ mA, pulse}$		0.18	0.4	V
				(-0.35)	(-0.6)	
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = (-)1.5\text{ A}, I_B = (-)75\text{ mA}$		(-)0.85	(-)1.2	V
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = (-)10\text{ }\mu\text{A}, I_E = 0$	(-)30			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = (-)1\text{ mA}, R_{BE} = \infty$	(-)25			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = (-)10\text{ }\mu\text{A}, I_C = 0$	(-)6			V

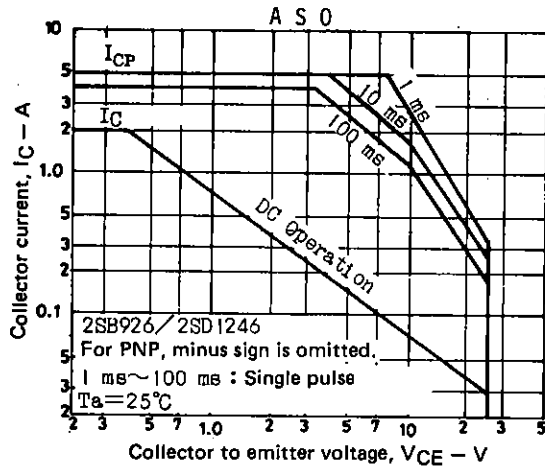
\* The 2SB926/2SD1246 are classified by 100 mA  $h_{FE}$  as follows:

100	R	200	140	S	280	200	T	400	280	U	560
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**Package Dimensions 2003A**  
(unit: mm)







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